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## Observation of crossing pores in anodically etched n-GaAs

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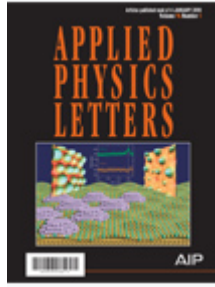
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### Abstract

Pores in GaAs in the micrometer range and oriented in  $|111|$  directions have been observed during the anodization of GaAs in aqueous HCl electrolytes. A direct evidence of pores intersection is presented which is a very promising feature for three-dimensional micro- and nanostructuring of III–V compounds for the production of photonic materials.

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